

Brandon Mitchell

List of Publications by Year in descending order

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papers

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758635

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all docs

30
docs citations

30
times ranked

262
citing authors

#	ARTICLE	IF	CITATIONS
1	Modeling defect mediated color-tunability in LEDs with Eu-doped GaN-based active layers. Journal of Applied Physics, 2022, 131, 045701.	1.1	2
2	On the connection between bound and scattering states of finite square-well potentials: a unified approach. European Journal of Physics, 2021, 42, 025405.	0.3	0
3	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. Journal of Applied Physics, 2020, 127, 013102.	1.1	6
4	Carrier dynamics and excitation of E_c in GaN. https://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" style="font-family: monospace;">E_c in GaN. https://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" style="font-family: monospace;">E_c in GaN.	1.1	11
5	Carrier dynamics and excitation of E_c in GaN. https://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" style="font-family: monospace;">E_c in GaN. https://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" style="font-family: monospace;">E_c in GaN.	1.5	17
6	Temporally modulated energy shuffling in highly interconnected nanosystems. Nanophotonics, 2020, 10, 851-876.	2.9	5
7	Picosecond time-resolved dynamics of energy transfer between GaN and the various excited states of E_c in GaN. https://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" style="font-family: monospace;">E_c in GaN. https://www.w3.org/1998/Math/MathML display="inline" overflow="scroll" style="font-family: monospace;">E_c in GaN.	1.1	3
8	Color-Tunability in GaN LEDs Based on Atomic Emission Manipulation under Current Injection. ACS Photonics, 2019, 6, 1153-1161.	3.2	15
9	Perspective: Toward efficient GaN-based red light emitting diodes using europium doping. Journal of Applied Physics, 2018, 123, .	1.1	100
10	A Fan-tastic Quantitative Exploration of Ohm's Law. Physics Teacher, 2018, 56, 75-78.	0.2	4
11	Re-Excitation of Trivalent Europium Ions Doped into Gallium Nitride Revealed through Photoluminescence under Pulsed Laser Excitation. ACS Photonics, 2018, 5, 875-880.	3.2	10
12	Quantitative study of energy-transfer mechanism in Eu,O-codoped GaN by time-resolved photoluminescence spectroscopy. Journal of Applied Physics, 2018, 123, 161419.	1.1	4
13	Measuring the practical particle-in-a-box: orthorhombic perovskite nanocrystals. European Journal of Physics, 2018, 39, 055501.	0.3	2
14	Detection of In segregation in InGaN by using Eu as a probe. Journal of Crystal Growth, 2017, 468, 831-834.	0.7	2
15	Synthesis and characterization of a liquid Eu precursor (EuC ₂ H ₂) allowing for valence control of Eu ions doped into GaN by organometallic vapor phase epitaxy. Materials Chemistry and Physics, 2017, 193, 140-146.	2.0	11
16	High-Power Eu-Doped GaN Red LED Based on a Multilayer Structure Grown at Lower Temperatures by Organometallic Vapor Phase Epitaxy. MRS Advances, 2017, 2, 159-164.	0.5	18
17	Charge state of vacancy defects in Eu-doped GaN. Physical Review B, 2017, 96, .	1.1	20
18	Emission enhancement and its mechanism of Eu-doped GaN by strain engineering. Optical Materials Express, 2017, 7, 1381.	1.6	10

#	ARTICLE	IF	CITATIONS
19	Growth of Eu-doped GaN and its magneto-optical properties. , 2016, , 259-280.		3
20	Enhanced photo/electroluminescence properties of Eu-doped GaN through optimization of the growth temperature and Eu related defect environment. APL Materials, 2016, 4, 056103.	2.2	22
21	Utilization of native oxygen in Eu(RE)-doped GaN for enabling device compatibility in optoelectronic applications. Scientific Reports, 2016, 6, 18808.	1.6	29
22	Substantial enhancement of red emission intensity by embedding Eu-doped GaN into a microcavity. AIP Advances, 2016, 6, .	0.6	15
23	Thermodynamics and Kinetics of Three Mg^{H} N^{V} Complexes in Mg:GaN from Combined First-Principles Calculation and Experiment. Physical Review Letters, 2014, 112, .	2.9	20
24	The role of donor-acceptor pairs in the excitation of Eu-ions in GaN:Eu epitaxial layers. Journal of Applied Physics, 2014, 115, .	1.1	45
25	Electron-beam-induced migration of hydrogen in Mg-doped GaN using Eu as a probe. Physical Review B, 2013, 88, .	1.1	15
26	Vibrationally induced center reconfiguration in co-doped GaN:Eu, Mg epitaxial layers: Local hydrogen migration vs. activation of non-radiative channels. Applied Physics Letters, 2013, 103, .	1.5	12
27	Excitation of Eu ³⁺ in gallium nitride epitaxial layers: Majority versus trap defect center. Applied Physics Letters, 2011, 98, 011102.	1.5	44
28	Enhanced magnetization in erbium doped GaN thin films due to strain induced electric fields. Applied Physics Letters, 2011, 99, 122506.	1.5	12